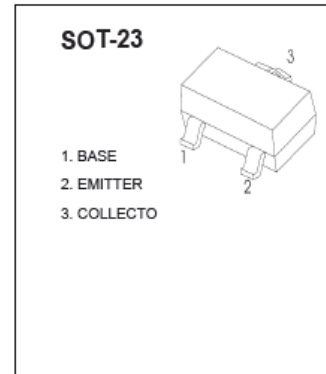


BC817

TRANSISTOR (NPN)

FEATURES

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC807 (PNP)
- Marking: **6A / 6B / 6C**



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	417	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C=10\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C=10\text{mA}, I_B=0$	45			V
Emitter-base breakdown voltage	V_{EBO}	$I_E=1\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=45\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	100		600	
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=1\text{V}, I_C=500\text{mA}$			1.2	V
Collector capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$		10		pF
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=10\text{mA}$ $f=100\text{MHz}$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	BC817-16	BC817-25	BC817-40
Range	100-250	160-400	250-600
Marking	6A	6B	6C

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TRANSISTOR (NPN)

